

MAC08BT1, MAC08MT1

Preferred Device

Sensitive Gate Triacs

Silicon Bidirectional Thyristors

Designed for use in solid state relays, MPU interface, TTL logic and other light industrial or consumer applications. Supplied in surface mount package for use in automated manufacturing.

- Sensitive Gate Trigger Current in Four Trigger Modes
- Blocking Voltage to 600 Volts
- Glass Passivated Surface for Reliability and Uniformity
- Surface Mount Package
- Device Marking: MAC08BT1: AC08B; MAC08MT1: A08M, and Date Code

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁽¹⁾ (Sine Wave, 50 to 60 Hz, Gate Open, $T_J = 25$ to 110°C) MAC08BT1 MAC08MT1	V_{DRM} , V_{RRM}	200 600	Volts
On-State Current RMS ($T_C = 80^\circ\text{C}$) (Full Sine Wave 50 to 60 Hz)	$I_T(\text{RMS})$	0.8	Amps
Peak Non-repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_C = 25^\circ\text{C}$)	I_{TSM}	8.0	Amps
Circuit Fusing Considerations (Pulse Width = 8.3 ms)	I^2t	0.4	A^2s
Peak Gate Power ($T_C = 80^\circ\text{C}$, Pulse Width $\leq 1.0 \mu\text{s}$)	P_{GM}	5.0	Watts
Average Gate Power ($T_C = 80^\circ\text{C}$, $t = 8.3 \text{ ms}$)	$P_{G(AV)}$	0.1	Watt
Operating Junction Temperature Range	T_J	-40 to $+110$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to $+150$	$^\circ\text{C}$

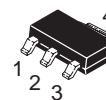
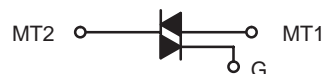
(1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



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TRIAC
0.8 AMPERE RMS
200 thru 600 VOLTS



SOT-223
CASE 318E
STYLE 11

PIN ASSIGNMENT

	PIN ASSIGNMENT
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

ORDERING INFORMATION

Device	Package	Shipping
MAC08BT1	SOT223	16mm Tape and Reel (1K/Reel)
MAC08MT1	SOT223	16mm Tape and Reel (1K/Reel)

Preferred devices are recommended choices for future use and best overall value.

MAC08BT1, MAC08MT1

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient PCB Mounted per Figure 1	$R_{\theta JA}$	156	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Tab Measured on MT2 Tab Adjacent to Epoxy	$R_{\theta JT}$	25	$^{\circ}\text{C}/\text{W}$
Maximum Device Temperature for Soldering Purposes (for 10 Seconds Maximum)	T_L	260	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Blocking Current ($V_D = \text{Rated } V_{\text{DRM}}, V_{\text{RRM}}; \text{Gate Open}$)	$I_{\text{DRM}}, I_{\text{RRM}}$	— —	— —	10 200	μA μA
$T_J = 25^{\circ}\text{C}$ $T_J = 110^{\circ}\text{C}$					

ON CHARACTERISTICS

Peak On-State Voltage ⁽¹⁾ ($I_T = \pm 1.1 \text{ A Peak}$)	V_{TM}	—	—	1.9	Volts
Gate Trigger Current (Continuous dc) All Quadrants ($V_D = 12 \text{ Vdc}, R_L = 100 \Omega$)	I_{GT}	—	—	10	mA
Holding Current (Continuous dc) ($V_D = 12 \text{ Vdc}, \text{Gate Open}, \text{Initiating Current} = \pm 20 \text{ mA}$)	I_{H}	—	—	5.0	mA
Gate Trigger Voltage (Continuous dc) All Quadrants ($V_D = 12 \text{ Vdc}, R_L = 100 \Omega$)	V_{GT}	—	—	2.0	Volts

DYNAMIC CHARACTERISTICS

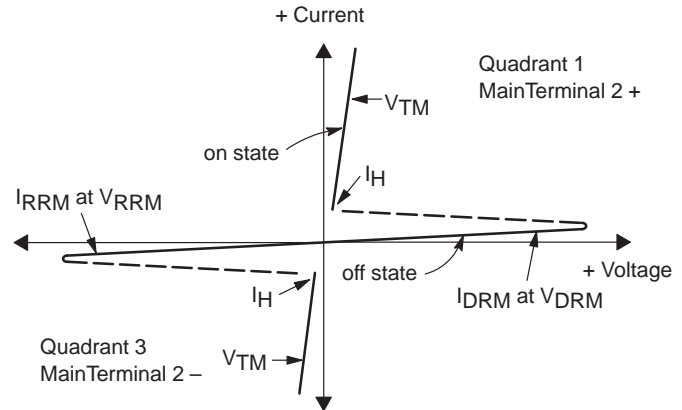
Critical Rate of Rise of Commutation Voltage ($f = 250 \text{ Hz}, I_{\text{TM}} = 1.0 \text{ A}, \text{Commutating } di/dt = 1.5 \text{ A/mS}$ On-State Current Duration = 2.0 mS, $V_{\text{DRM}} = 200 \text{ V}$, Gate Unenergized, $T_C = 110^{\circ}\text{C}$, Gate Source Resistance = 150 Ω , See Figure 10)	$(dv/dt)_C$	1.5	—	—	$\text{V}/\mu\text{s}$
Critical Rate-of-Rise of Off State Voltage ($V_{\text{pk}} = \text{Rated } V_{\text{DRM}}, T_C = 110^{\circ}\text{C}, \text{Gate Open}, \text{Exponential Method}$)	dv/dt	10	—	—	$\text{V}/\mu\text{s}$

(1) Pulse Test: Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

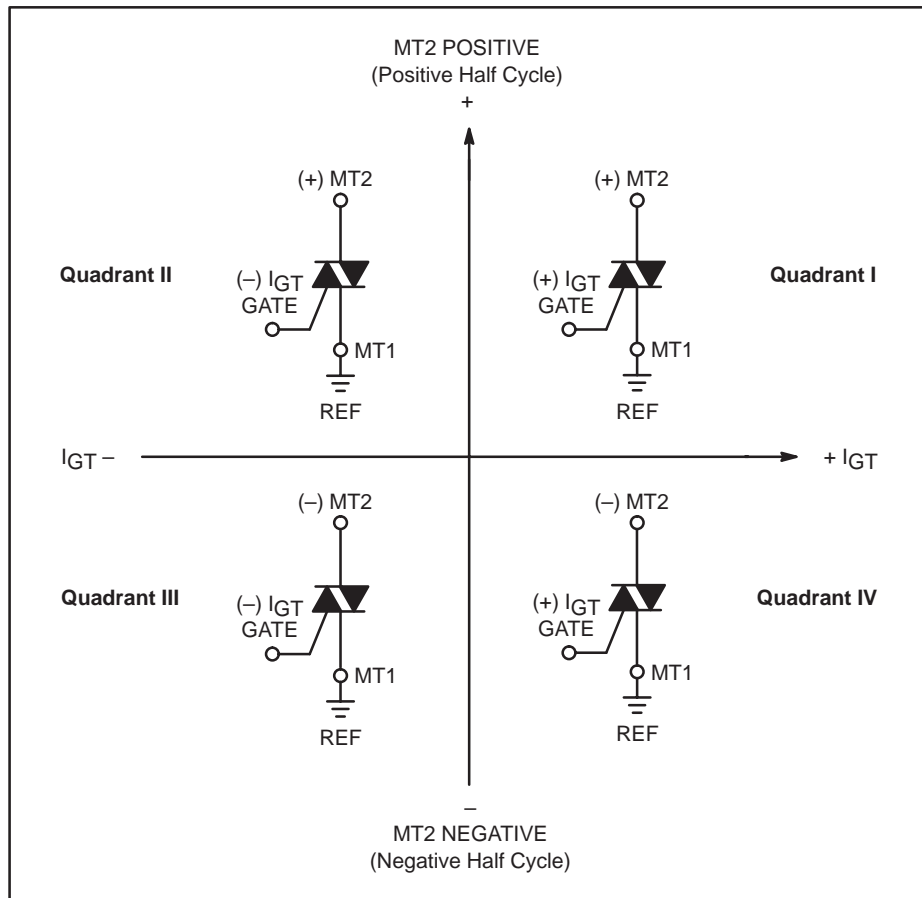
MAC08BT1, MAC08MT1

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



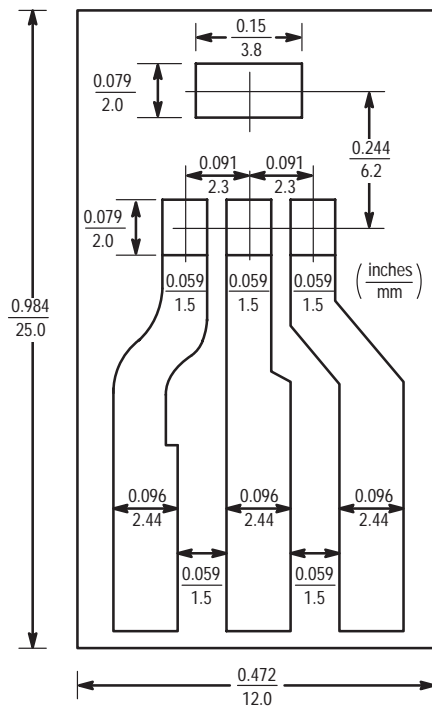
Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

MAC08BT1, MAC08MT1



BOARD MOUNTED VERTICALLY IN CINCH 8840 EDGE CONNECTOR.
 BOARD THICKNESS = 65 MIL., FOIL THICKNESS = 2.5 MIL.
 MATERIAL: G10 FIBERGLASS BASE EPOXY

Figure 1. PCB for Thermal Impedance and Power Testing of SOT-223

MAC08BT1, MAC08MT1

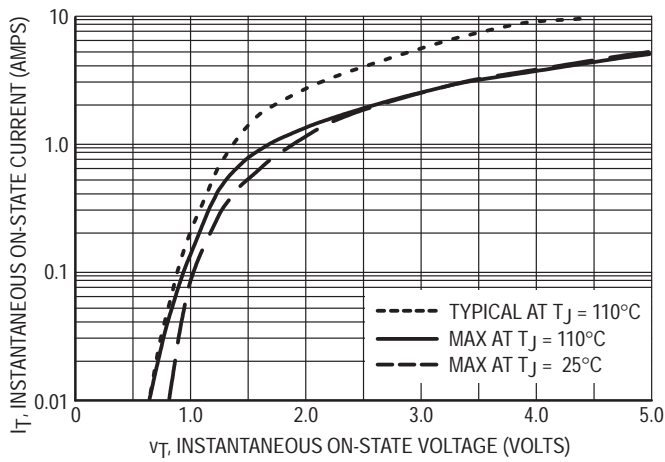


Figure 2. On-State Characteristics

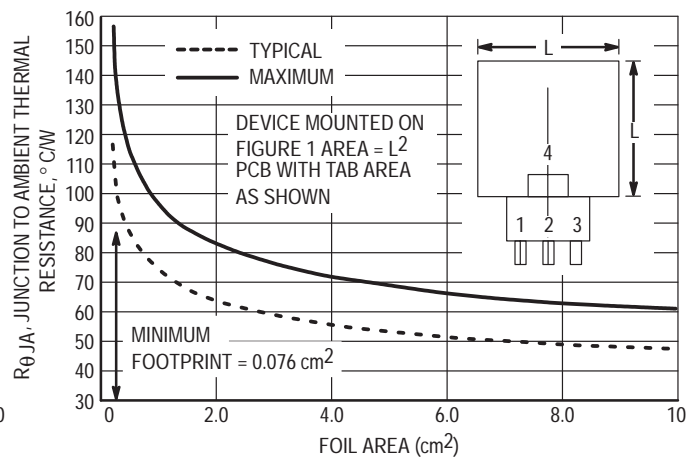
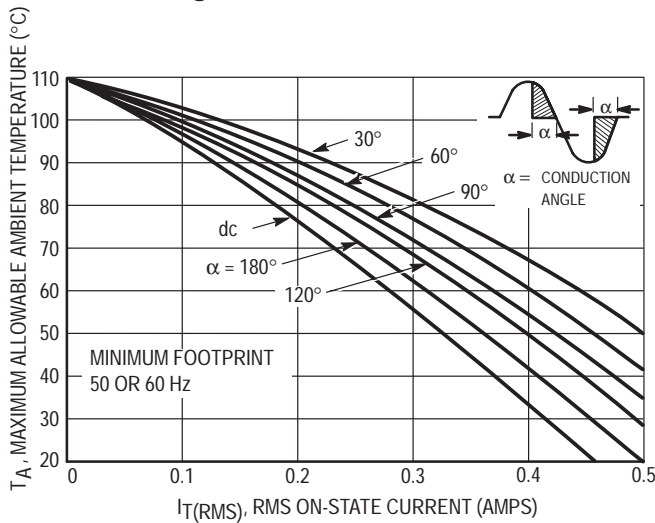
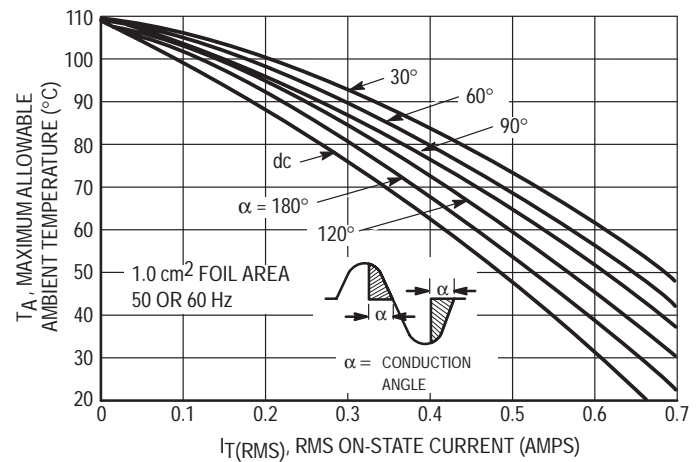


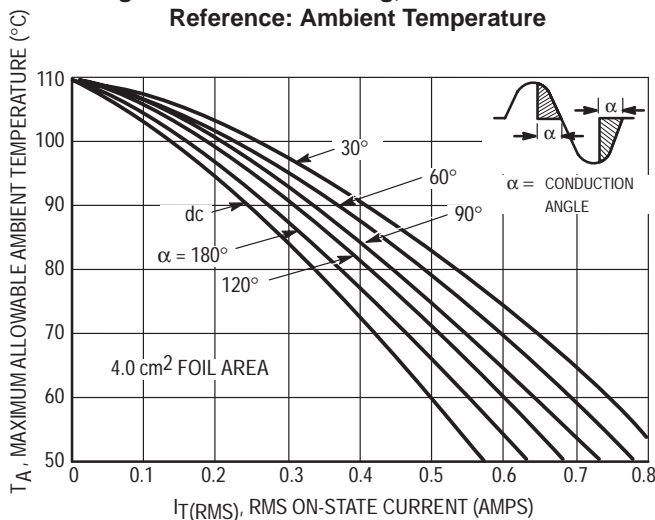
Figure 3. Junction to Ambient Thermal Resistance versus Copper Tab Area



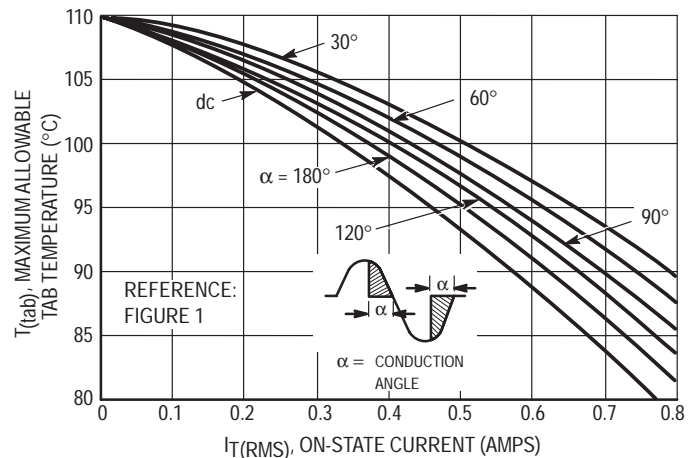
**Figure 4. Current Derating, Minimum Pad Size
Reference: Ambient Temperature**



**Figure 5. Current Derating, 1.0 cm Square Pad
Reference: Ambient Temperature**



**Figure 6. Current Derating, 2.0 cm Square Pad
Reference: Ambient Temperature**



**Figure 7. Current Derating
Reference: MT2 Tab**

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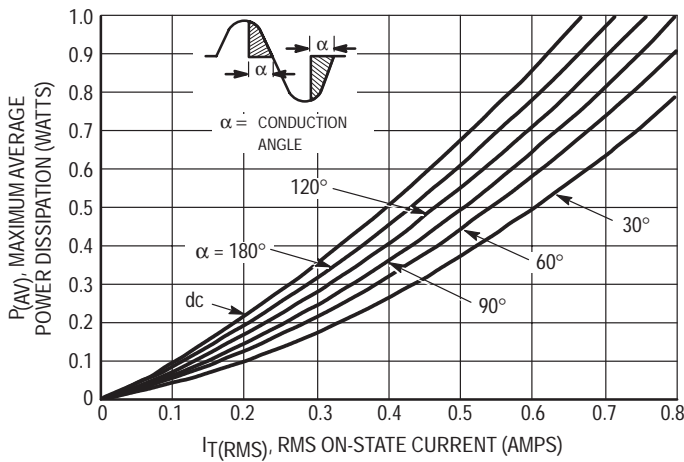


Figure 8. Power Dissipation

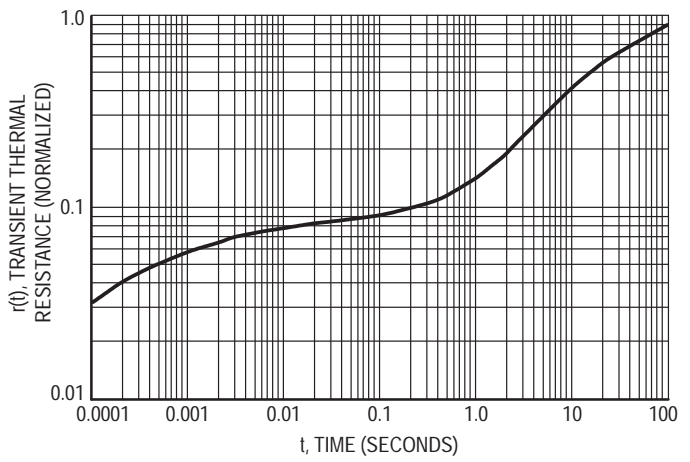
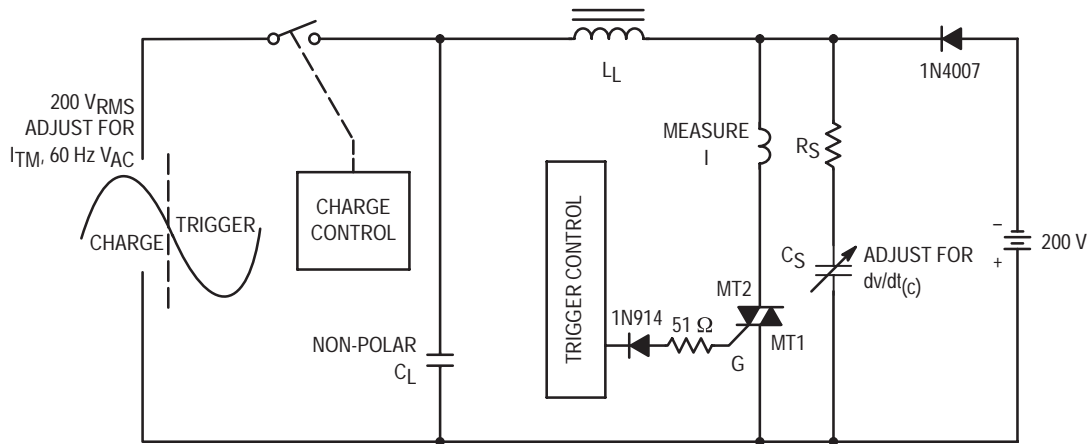


Figure 9. Thermal Response, Device Mounted on Figure 1 Printed Circuit Board



Note: Component values are for verification of rated $(dv/dt)_C$. See AN1048 for additional information.

Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Voltage $(dv/dt)_C$

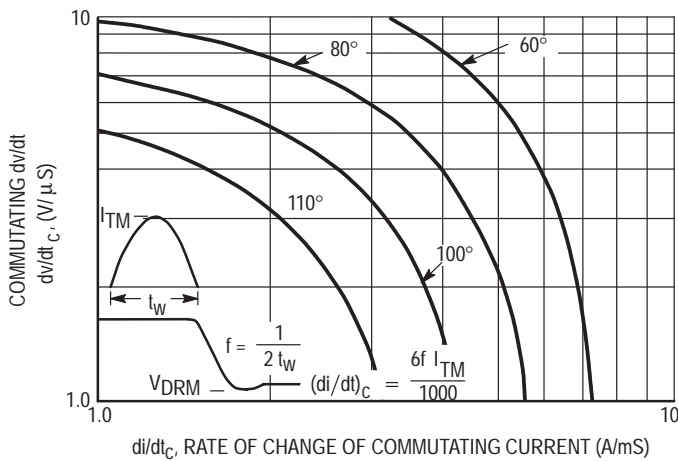


Figure 11. Typical Commutating dv/dt versus Current Crossing Rate and Junction Temperature

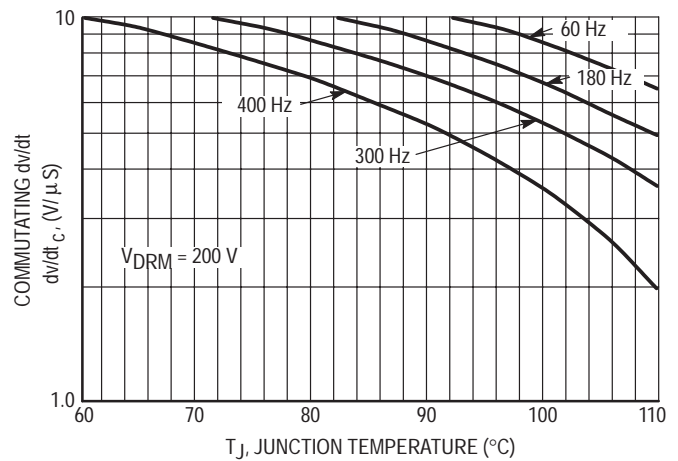


Figure 12. Typical Commutating dv/dt versus Junction Temperature at 0.8 Amps RMS

MAC08BT1, MAC08MT1

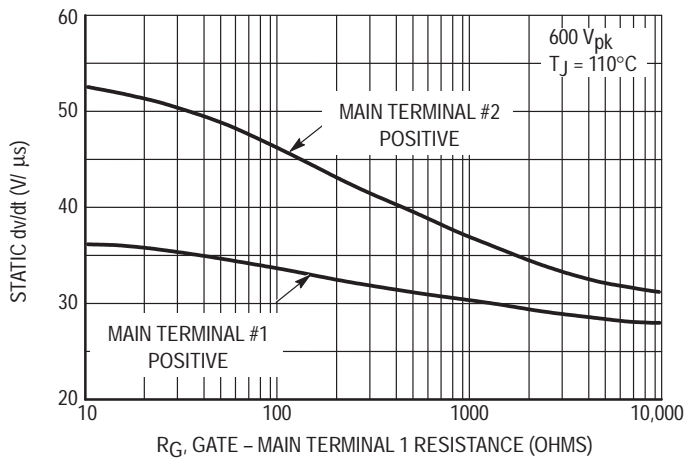


Figure 13. Exponential Static dv/dt versus Gate – Main Terminal 1 Resistance

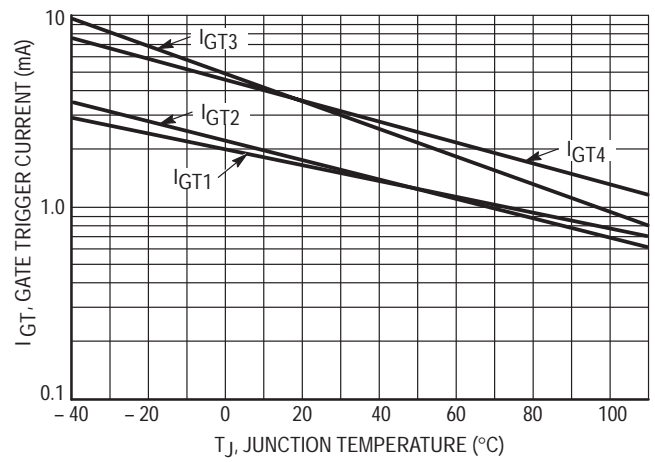


Figure 14. Typical Gate Trigger Current Variation

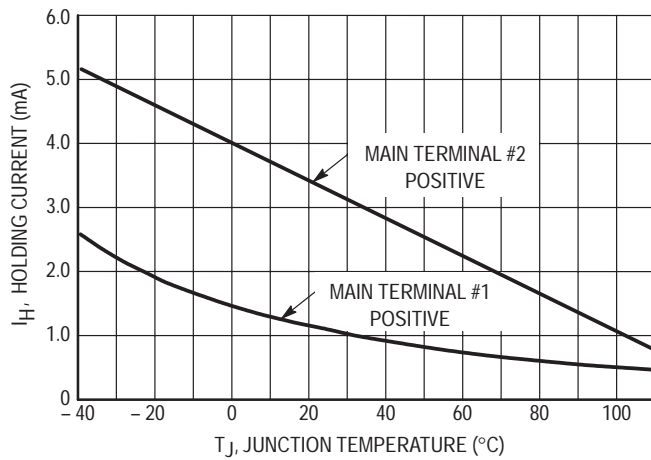


Figure 15. Typical Holding Current Variation

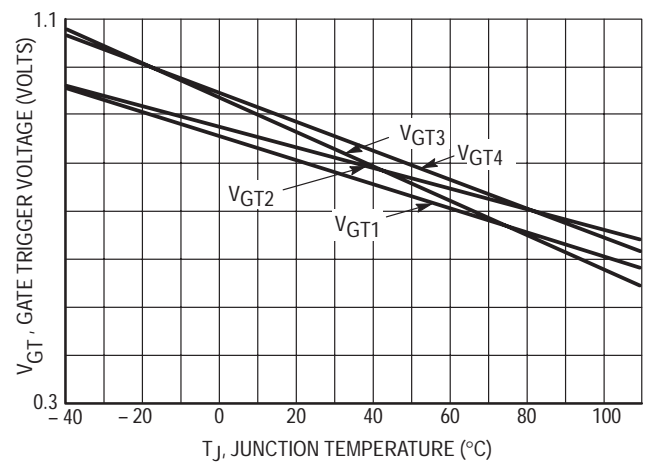


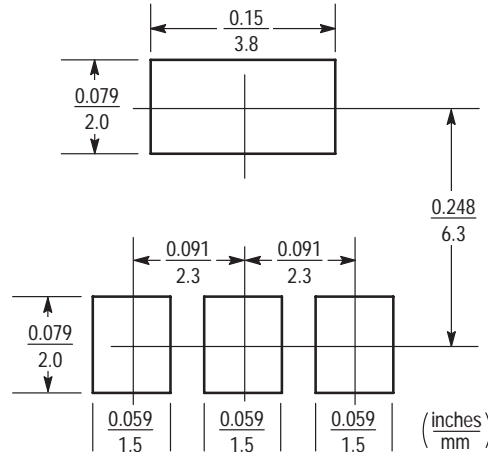
Figure 16. Gate Trigger Voltage Variation

INFORMATION FOR USING THE SOT-223 SURFACE MOUNT PACKAGE

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



SOT-223

SOT-223 POWER DISSIPATION

The power dissipation of the SOT-223 is a function of the MT2 pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient, and the operating temperature, T_A . Using the values provided on the data sheet for the SOT-223 package, P_D can be calculated as follows:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T_A of 25°C, one can calculate the power dissipation of the device which in this case is 550 milliwatts.

$$P_D = \frac{110^\circ\text{C} - 25^\circ\text{C}}{156^\circ\text{C/W}} = 550 \text{ milliwatts}$$

The 156°C/W for the SOT-223 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 550 milliwatts. There are other alternatives to achieving higher power dissipation from the SOT-223 package. One is to increase the area of the MT2 pad. By increasing the area of the MT2 pad, the power dissipation can be increased. Although one can almost double the power dissipation with this method, one will be giving up area on the printed circuit board which can defeat the purpose of using surface mount technology. A graph of $R_{\theta JA}$ versus MT2 pad area is shown in Figure 3.

Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad™. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

SOLDER STENCIL GUIDELINES

Prior to placing surface mount components onto a printed circuit board, solder paste must be applied to the pads. A solder stencil is required to screen the optimum amount of solder paste onto the footprint. The stencil is made of brass

or stainless steel with a typical thickness of 0.008 inches. The stencil opening size for the SOT-223 package should be the same as the pad size on the printed circuit board, i.e., a 1:1 registration.

SOLDERING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference should be a maximum of 10°C.

- The soldering temperature and time should not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient should be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.

* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

TYPICAL SOLDER HEATING PROFILE

For any given circuit board, there will be a group of control settings that will give the desired heat pattern. The operator must set temperatures for several heating zones, and a figure for belt speed. Taken together, these control settings make up a heating “profile” for that particular circuit board. On machines controlled by a computer, the computer remembers these profiles from one operating session to the next. Figure 17 shows a typical heating profile for use when soldering a surface mount device to a printed circuit board. This profile will vary among soldering systems but it is a good starting point. Factors that can affect the profile include the type of soldering system in use, density and types of components on the board, type of solder used, and the type of board or substrate material being used. This profile shows temperature versus time.

The line on the graph shows the actual temperature that might be experienced on the surface of a test board at or near a central solder joint. The two profiles are based on a high density and a low density board. The Vitronics SMD310 convection/infrared reflow soldering system was used to generate this profile. The type of solder used was 62/36/2 Tin Lead Silver with a melting point between 177–189°C. When this type of furnace is used for solder reflow work, the circuit boards and solder joints tend to heat first. The components on the board are then heated by conduction. The circuit board, because it has a large surface area, absorbs the thermal energy more efficiently, then distributes this energy to the components. Because of this effect, the main body of a component may be up to 30 degrees cooler than the adjacent solder joints.

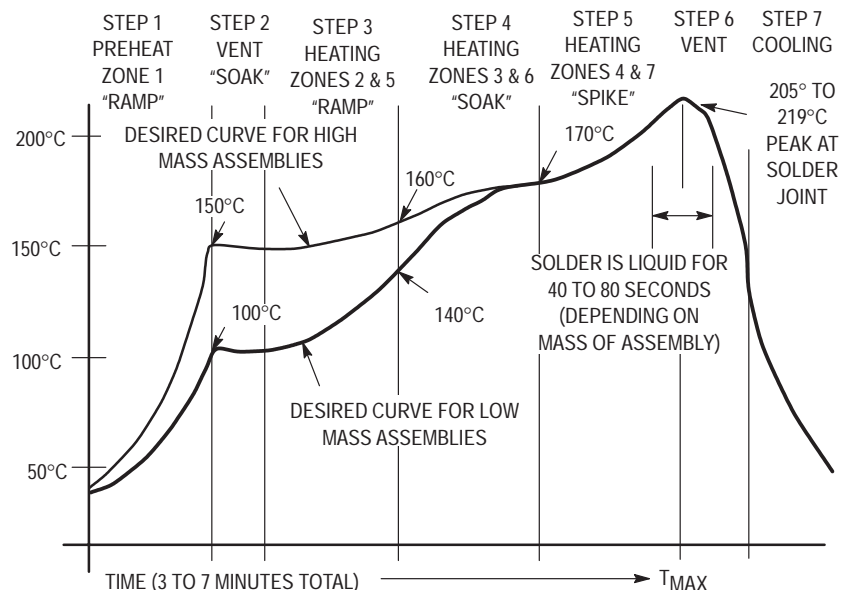
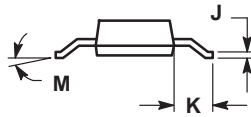
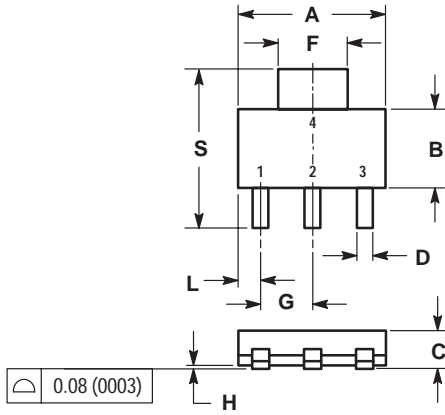


Figure 17. Typical Solder Heating Profile

MAC08BT1, MAC08MT1

PACKAGE DIMENSIONS

SOT-223
CASE 318E-04
ISSUE J



NOTES:


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.249	0.263	6.30	6.70
B	0.130	0.145	3.30	3.70
C	0.060	0.068	1.50	1.75
D	0.024	0.035	0.60	0.89
F	0.115	0.126	2.90	3.20
G	0.087	0.094	2.20	2.40
H	0.0008	0.0040	0.020	0.100
J	0.009	0.014	0.24	0.35
K	0.060	0.078	1.50	2.00
L	0.033	0.041	0.85	1.05
M	0°	10°	0°	10°
S	0.264	0.287	6.70	7.30

STYLE 11:

- PIN 1. MT 1
- MT 2
- GATE
- MT 2

Notes

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